

PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Masateru NAKAMURA

Application No.: New U.S. National Stage of PCT/JP2004/017562

Filed: January 31, 2006

Docket No.: 126868

For: METHOD OF PRODUCTION OF SILICON CARBIDE SINGLE CRYSTAL

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

Pursuant to 37 CFR §1.56, the attention of the Patent and Trademark Office is hereby directed to the references listed on the attached PTO-1449. Unless otherwise indicated herein, one copy of each reference is attached. It is respectfully requested that the information be expressly considered during the prosecution of this application, and that the references be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

- ☒ 1. This Information Disclosure Statement is being filed (a) within three months of the U.S. filing date of this non-CPA application, OR (b) before the mailing date of a first Office Action on the merits in the present application. No certification or fee is required.
- ☒ 2. Relevance of one or more non-English language reference is discussed in the present specification. See Reference 2.
- ☒ 3. One or more reference cited herein was cited in the International Search Report. An English language version of the International Search Report is attached for the Examiner's information.
- ☒ 4. In accordance with 37 CFR §1.98(a)(2)(ii), copies of any U.S. patents and patent application publications are not attached.
- ☒ 5. An English language Abstract of one or more non-English language reference is attached hereto. See References 2-3.

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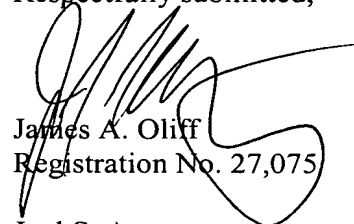
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6. A computer-generated English language translation of one or more Japanese Patent Publication cited herein has been obtained from the website of the Japanese Patent Office ([<http://www.jpo.go.jp>]), and is attached, but has not been reviewed for accuracy. See References 2-3.

Respectfully submitted,



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Date: January 31, 2006

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 Sheet 1 of 1

Form PTO-1449 (REV. 1/06)		US Dept. of Commerce PATENT & TRADEMARK OFFICE		ATTY DOCKET NO. 126868		APPLICATION NO. New U.S. National Stage of PCT/JP2004/017562	
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)				APPLICANT Masateru NAKAMURA			
				FILING DATE January 31, 2006			

U.S. PATENT DOCUMENTS				
Examiner Initials	Cite No.	Document Number	Date	Name
	1.	US 4,349,407	9/14/1982	Lundberg

FOREIGN PATENT DOCUMENTS						
Examiner Initials	Cite No.	Document Number	Date	Country	With English Abstract	With English Translation
	2.	JP A 2000-264790	9/26/2000	JAPAN	X	X
	3.	JP A 2004-315281	11/11/2004	JAPAN	X	X

OTHER DOCUMENTS		
Examiner Initials	Cite No.	(Including Author, Title, Date, Pertinent Pages, etc.)
	4.	Hoffman, D. H., et al. "Prospects of the use of liquid phase techniques for the growth of bulk silicon carbide crystals" MATERIALS SCIENCE AND ENGINEERING B, ELSEVIER SEQUOIA, LAUSANNE, CH, vol. 61-62, 30 July 1999 (1999-07-30), pages 29-39, XP004363298 ISSN: 0921-5107.

EXAMINER	DATE CONSIDERED
Examiner: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	

Date: January 31, 2006